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Vishay Siliconix

Automotive P-Channel 40 V (D-S) 175 °C MOSFET



FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R_q and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

P-Channel MOSFET



PRODUCT SUMMARY				
V _{DS} (V)	-40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.0034			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.0048			
I _D (A)	-120			
Configuration	Single			
Package	TO-263			

ABSOLUTE MAXIMUM RATING	43 (1C = 25 °C, unless		1)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V_{DS}	-40	V	
Gate-source voltage		V_{GS}	± 20	V	
Continuo durin cumont	$T_{\rm C} = 25 ^{\circ}{\rm C}^{\rm a}$ $T_{\rm C} = 125 ^{\circ}{\rm C}$	1	-120		
Continuous drain current	T _C = 125 °C	- I _D	-90		
Continuous source current (diode conducti	on) ^a	Is	-120	Α	
Pulsed drain current ^b		I _{DM}	-315		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-51		
Single pulse avalanche energy	L=U.I IIIH	E _{AS}	130	mJ	
Martin and a state to the b	T _C = 25 °C	В	157	W	
Maximum power dissipation ^b	T _C = 125 °C	P_{D}	52		
Operating junction and storage temperature	e range	T _J , T _{stq}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS							
PARAMETER		SYMBOL	LIMIT	UNIT			
Junction-to-ambient	PCB mount c	R _{thJA}	40	°C/W			
Junction-to-case (drain)		R_{thJC}	0.95	C/VV			

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0$, $I_D = -250 \mu A$		-40	-	-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$		-	-2.5	V	
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
	I _{DSS}	V _{GS} = 0 V	V _{DS} = -40 V	-	-	-1		
Zero gate voltage drain current		$V_{GS} = 0 V$	$V_{DS} = -40 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$	-	-	-50	μA	
		$V_{GS} = 0 V$	$V_{DS} = -40 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$	-	-	-250		
On-state drain current a	I _{D(on)}	V _{GS} = -10 V	$V_{GS} = -10 \text{ V}$ $V_{DS} \le -5 \text{ V}$		-	-	Α	
	,	V _{GS} = -10 V	I _D = -25 A	-	0.00283	0.00340	Ω	
Drain actives on state registance 3	В	V _{GS} = -10 V	I _D = -25 A, T _J = 125 °C	-	-	0.00520		
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -10 V	I _D = -25 A, T _J = 175 °C	-	-	0.00620		
		V _{GS} = -4.5 V	I _D = -20 A	-	0.00400	0.00480	Ì	
Forward transconductance a	9fs	V _{DS} = -15 V, I _D = -25 A		-	92	-	S	
Dynamic ^b								
Input capacitance	C _{iss}		V _{DS} = -25 V, f = 1 MHz	-	17 027	23 600	pF	
Output capacitance	Coss	$V_{GS} = 0 V$		-	1487	2100		
Reverse transfer capacitance	C_{rss}			-	1079	1500		
Total gate charge ^c	Qg		V _{DS} = -20 V, I _D = -60 A	-	288	450	nC	
Gate-source charge ^c	Q _{gs}	V _{GS} = -10 V		-	66	-		
Gate-drain charge ^c	Q _{gd}			-	52	-		
Gate resistance	R_g	f = 1 MHz		1.3	2.65	4	Ω	
Turn-on delay time ^c	t _{d(on)}			-	18	30		
Rise time ^c	t _r	$V_{DD} = -20 \text{ V}, \text{ R}_L = 0.33 \Omega$ $I_D \cong -60 \text{ A}, \text{ V}_{GEN} = -10 \text{ V}, \text{ R}_g = 1 \Omega$		-	20	40	ns	
Turn-off delay time ^c	t _{d(off)}			-	155	300		
Fall time ^c	t _f			-	135	250		
Source-Drain Diode Ratings and Charac	teristics ^b							
Pulsed current ^a	I _{SM}			-	-	-315	Α	
Forward voltage	V _{SD}	I _F = -50 A, V _{GS} = 0 V		-	-0.85	-1.5	V	
Body diode reverse recovery time	t _{rr}	I _F = -50 A, di/dt = 100 A/μs		-	33	70	ns	
Body diode reverse recovery charge	Q _{rr}			-	29	60	nC	
Reverse recovery fall time	ta			-	18	-		
Reverse recovery rise time	t _b			-	15	-	ns	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1.7	-	Α	

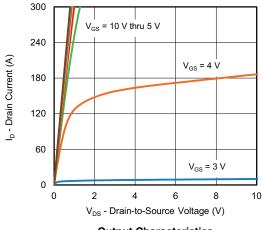
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

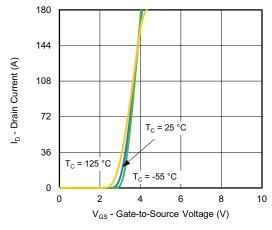
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



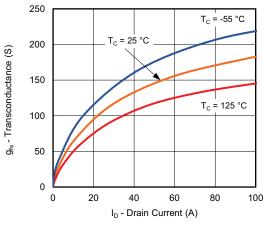
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



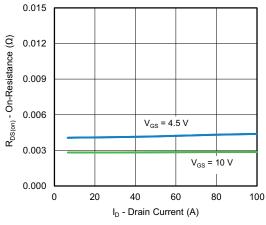
Output Characteristics



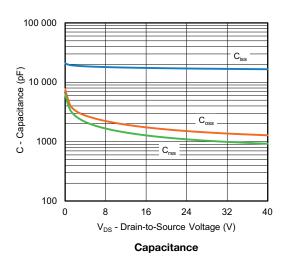
Transfer Characteristics

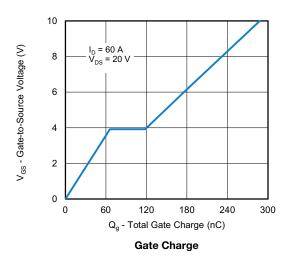


Transconductance



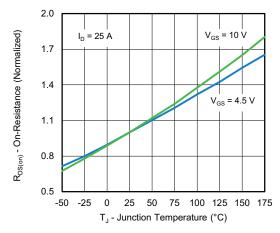
On-Resistance vs. Drain Current



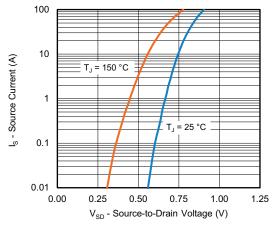




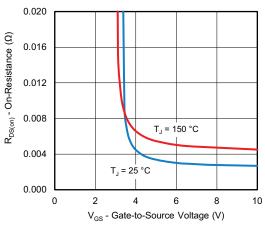
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



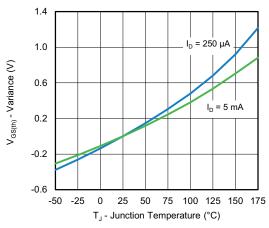
On-Resistance vs. Junction Temperature



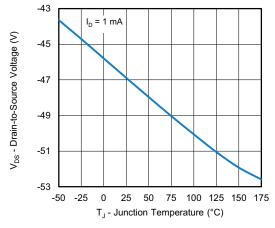
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



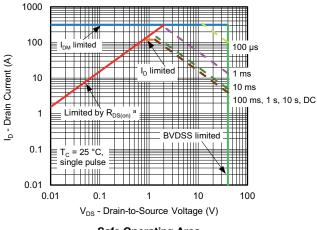
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



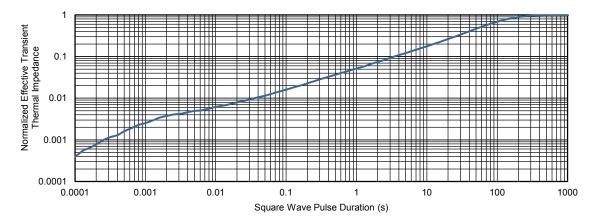
THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



Safe Operating Area

Note

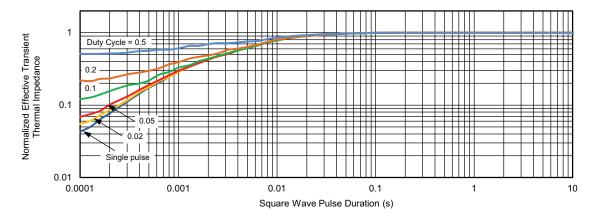
a. $V_{GS} > \mbox{minimum} \ V_{GS}$ at which $R_{DS(on)}$ is specified



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg277450.



TO-263 (D²PAK): 3-LEAD









DETAIL A (ROTATED 90°)



⋝:	,	 	b— b1–		ļ	ļ
2:	П				5	ပ
	SE	СТ	ION	ΙΔ.	- 1 - Δ	Ŧ

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6 This feature is for thick lead.

		INCHES		MILLIMETERS		
DIM.		MIN.	MAX.	MIN.	MAX.	
	Α	0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
D2		0.038	0.042	0.965	1.067	
D3		0.045	0.055	1.143	1.397	
D4		0.044	0.052	1.118	1.321	
	Е	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
е		0.100	BSC	2.54 BSC		
K		0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		L2 0.040		1.016	1.397	
L3		0.050	0.070	1.270	1.778	
	L4 0		0 BSC 0.254 BS		BSC	
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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